NSN 5961-01-307-2490

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-307-2490 **Inclosure Material:** Ceramic **Overall Length:** 3.640 inches **Overall Height:** 1.280 inches Overall Width: 0.805 inches **Component Name And Quantity:** 2 semiconductor device thyristor **Mounting Method:** Press fit **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon all semiconductor device thyristor **Voltage Rating In Volts Per Characteristic:** 1700.0 nonrepetitive peak reverse voltage all semiconductor device thyristor and 1400.0 repetitive peak reverse voltage all semiconductor device thyristor and 1400.0 repetitive peak off-state voltage all semiconductor device thyristor **Current Rating Per Characteristic:** 145.00 amperes forward current, total rms horsepower metric all semiconductor device thyristor **Power Rating Per Characteristic:** 16.0 watts small-signal input power, common-collector blank all semiconductor device thyristor **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** All semiconductor deivce thyristor junction pattern arrangement: pnpn **Terminal Type And Quantity:** 4 tab w/screw Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: